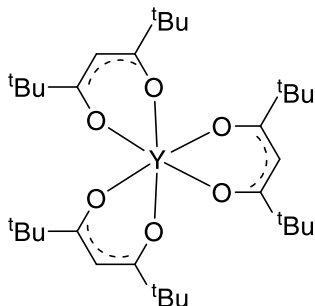


Catalog # 39-1000 Tris(2,2,6,6-tetramethyl-3,5-heptanedionato)yttrium(III), 98+% (99.9%-Y) (REO)  
[Y(TMHD)3]



Thermal Behavior:

- Melting point 170-173°C, 166-169°C [1]
- TGA diagram and data is available in [2]
- Vapor pressure: 0.05 Torr at 95°C [3]

Technical Notes:

1. ALD/CVD precursor and dopant for yttrium containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Y <sub>2</sub> O <sub>3</sub>	ALD PE-ALD	120°C 200°C	1.5-2.25 Torr -	O <sub>3</sub> P <sub>2</sub> O <sub>5</sub>	200-425°C 200-300°C	2 3-4
YF <sub>3</sub>	ALD	150°C	<7.5 Torr	TiF <sub>4</sub>	175-325°C	5
Y <sub>x</sub> Sc <sub>y</sub> O <sub>3</sub>	ALD	125°C	1.5-2.25 Torr	Sc(thmd) <sub>3</sub> ; O <sub>3</sub>	335-350°C	6
Y <sub>x</sub> Ce <sub>y</sub> O <sub>3</sub>	ALD	-	0.75-2.25 Torr	Ce(thmd) <sub>4</sub> ; O <sub>3</sub>	300°C	7
Y <sub>x</sub> Zr <sub>y</sub> O <sub>3</sub>	ALD	-	1.5-2.25 Torr	Cp <sub>2</sub> ZrCl <sub>2</sub> , Cp <sub>2</sub> ZrMe <sub>2</sub> , Zr(thd) <sub>4</sub> ; O <sub>3</sub>	275-375°C	8
Y <sub>x</sub> Mn <sub>y</sub> O <sub>3</sub>	RE-ALD	-	-	Mn(TMHD) <sub>3</sub> ; O <sub>3</sub>	250°C	9
YVO <sub>4</sub> :YbVO <sub>4</sub>	ALD	128°C	2.1 Torr	VO(thd) <sub>2</sub> , Yb(thd) <sub>3</sub> ; O <sub>3</sub>	260-300°C	10

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